



Electrical Features

- Trench/Fieldstop IGBT
- V_{CEsat} with positive Temperature Coefficient
- Low V_{CEsat}

Typical Applications

- Auxiliary inverters
- Motor drives
- Servo drives



Mechanical Features

- High power density
- Integrated NTC temperature sensor
- Copper base plate
- Solder contact technology
- Standard housing

IGBT, Inverter

Maximum Rated Values							
Symbol	Item	Conditions	Rating	Unit			
IGBT							
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1200	V			
V_{GES}	Gate-emitter voltage	-	± 20	V			
I_C	Collector current,DC	$T_C=100^{\circ}C, T_{vj}=175^{\circ}C$	75	A			
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	150	A			
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	384	W			
Characteristics Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA	
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	500	nA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=2.4mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.60	6.2	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C=75A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	1.92	2.3	V
			$T_{vj}=125^{\circ}C$	-	2.21	-	
			$T_{vj}=150^{\circ}C$	-	2.31	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	5.30	-	nF	
C_{oes}	Output capacitance		-	0.35	-		
C_{res}	Reverse transfer capacitance		-	0.18	-		
Q_G	Gate charge	$V_{CC}=600V, I_C=75A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	0.477	-	μC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	2.4	-	Ω	

t _{d(on)}	Turn-on delay time	V _{CC} =600V I _C =75A V _{GE} =±15V R _{G(on)} =10Ω R _{G(off)} =10Ω	T _{vj} =25°C	-	63.4	-	ns	
			T _{vj} =125°C	-	61.8	-		
			T _{vj} =150°C	-	60.5	-		
t _r	Rise time		T _{vj} =25°C	-	60.1	-		
			T _{vj} =125°C	-	65.1	-		
			T _{vj} =150°C	-	65.6	-		
t _{d(off)}	Turn-off delay time		T _{vj} =25°C	-	235.6	-		
			T _{vj} =125°C	-	240.1	-		
			T _{vj} =150°C	-	272.8	-		
t _f	Fall time		T _{vj} =25°C	-	175.2	-		
			T _{vj} =125°C	-	248.8	-		
			T _{vj} =150°C	-	396.8	-		
E _{on}	Turn-on energy (per pulse)	V _{CC} =600V, I _C =75A V _{GE} =±15V, R _{G(on)} =10Ω di/dt=4300A/μs(T _{vj} =150°C)	T _{vj} =25°C	-	9.60	-	mJ	
			T _{vj} =125°C	-	11.61	-		
			T _{vj} =150°C	-	12.47	-		
E _{off}	Turn-off energy (per pulse)		V _{CC} =600V, I _C =75A V _{GE} =±15V, R _{G(off)} =10Ω du/dt=6200V/μs(T _{vj} =150°C)	T _{vj} =25°C	-	4.13		-
				T _{vj} =125°C	-	5.10		-
				T _{vj} =150°C	-	5.40		-
SC data	Short-circuit current	V _{CC} =600V, V _{GE} ≤15V, T _{vj} =25°C V _{CES} ≤1200V, t _p ≤10μs		-	460	-	A	
R _{thJC}	Thermal resistance, junction to case	Per IGBT		-	-	0.39	K/W	
R _{thCH}	Thermal resistance, case to heatsink	Per IGBT / λgrease=1W/(m·K)		-	0.13	-	K/W	
T _{vjop}	Temperature under switching conditions			-40		150	°C	
Diode, Inverter								
Maximum Rated Values								
Symbol	Item	Conditions			Rating	Unit		
V _{RRM}	Repetitive peak reverse voltage	T _{vj} =25°C			1200	V		
I _F	Forward current, DC				75	A		
I _{FRM}	Repetitive peak forward current	t _p =1ms			150	A		
I ² t	I ² t-value	V _R =0V, t _p =10ms, T _{vj} =125°C			1200	A ² s		
Characteristic Values								
V _F	Continuous forward voltage	I _F =75A V _{GE} =0V	T _{vj} =25°C	-	1.95	2.3	V	
			T _{vj} =125°C	-	1.59	-		
			T _{vj} =150°C	-	1.58	-		
I _{RM}	Peak reverse recovery current		T _{vj} =25°C	-	61.6	-	A	
			T _{vj} =125°C	-	67.2	-		
			T _{vj} =150°C	-	68.8	-		
t _{rr}	Reverse recovery time	I _F =75A V _{GE} =-15V -di _F /dt=2200A/μs (T _{vj} =150°C)	T _{vj} =25°C	-	113.2	-	ns	
			T _{vj} =125°C	-	444.8	-		
			T _{vj} =150°C	-	486.6	-		
Q _r	Recovered charge		T _{vj} =25°C	-	5.99	-	μC	
			T _{vj} =125°C	-	11.91	-		
			T _{vj} =150°C	-	13.55	-		

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	2.67	-	mJ
			T _{vj} =125°C	-	4.53	-	
			T _{vj} =150°C	-	5.18	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	0.67	-	K/W
R _{thCH}	Thermal resistance, case to heatsink	per diode / λ _{grease} =1 W/(m • K)	-	0.205	-	-	K/W
T _{vjop}	Temperature under switching conditions		-40		150		°C

Diode, Rectifier

Maximum Rated Values							
Symbol	Item	Conditions		Rating			Unit
V _{RRM}	Repetitive peak reverse voltage	T _{vj} =25°C		1800			V
I _{FRMSM}	Maximum RMS forward current per chip	T _C =80°C, T _{vj} =175°C		75			A
I _{RMSM}	Maximum RMS current at rectifier output	T _C = 80°C		150			A
I _{FSM}	Surge forward current	tp = 10 ms, T _{vj} =150°C		470			A
I ² t	I ² t-value	V _R =0V, t _p =10ms, T _{vj} =150°C		1100			A ² s
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
V _F	Continuous forward voltage	I _F =75A V _{GE} =0V	T _{vj} =25°C	-	1.28	1.6	V
			T _{vj} =125°C	-	1.14	-	
			T _{vj} =150°C	-	1.12	-	
I _R	Reverse current	V _R =1800V	T _{vj} =25°C	-	-	10	uA
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
T _{vjop}	Temperature under switching conditions		-40		150		°C

IGBT, Brake-Chopper

Maximum Rated Values							
Symbol	Item	Conditions		Values			Unit
V _{CES}	Collector-emitter voltage	T _{vj} =25°C		1200			V
V _{GES}	Gate-emitter voltage	-		±20			V
I _C	Collector current,DC	T _C =100°C, T _{vj} =175°C		50			A
I _{CRM}	Repetitive peak collector current	t _p =1ms		100			A
P _{tot}	Total power dissipation	T _C =25°C, T _{vj} =175°C		258			W
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
IGBT			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =1200V, V _{GE} =0V, T _{vj} =25°C	-	-	1	mA	
I _{GES}	Gate leakage current	V _{CE} =0V, V _{GE} =20V, T _{vj} =25°C	-	-	500	nA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =1.5mA, V _{CE} =V _{GE} , T _{vj} =25°C	5.2	5.5	6.2	V	

V_{CEsat}	Collector-emitter saturation voltage	$I_C=50A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	2.04	2.3	
			$T_{vj}=125^{\circ}C$	-	2.41	-	
			$T_{vj}=150^{\circ}C$	-	2.51	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$		-	3.15	-	nF
C_{oes}	Output capacitance			-	0.18	-	
C_{res}	Reverse transfer capacitance			-	0.103	-	
Q_G	Gate charge	$V_{CC}=600V, I_C=50A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$		-	0.316	-	μC
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$		-	-	-	Ω
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $I_C=50A$ $V_{GE}=\pm 15V$ $R_{G(on)}=10\Omega$ $R_{G(off)}=10\Omega$	$T_{vj}=25^{\circ}C$	-	30.4	-	ns
			$T_{vj}=125^{\circ}C$	-	14.8	-	
			$T_{vj}=150^{\circ}C$	-	14.4	-	
t_r	Rise time		$T_{vj}=25^{\circ}C$	-	60.3	-	
			$T_{vj}=125^{\circ}C$	-	64.1	-	
			$T_{vj}=150^{\circ}C$	-	64.1	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^{\circ}C$	-	176.8	-	
			$T_{vj}=125^{\circ}C$	-	218.8	-	
			$T_{vj}=150^{\circ}C$	-	239.6	-	
t_f	Fall time	$T_{vj}=25^{\circ}C$	-	384.8	-		
		$T_{vj}=125^{\circ}C$	-	468.1	-		
		$T_{vj}=150^{\circ}C$	-	489.6	-		
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^{\circ}C$	-	3.53	-	mJ	
		$T_{vj}=125^{\circ}C$	-	5.44	-		
		$T_{vj}=150^{\circ}C$	-	5.95	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^{\circ}C$	-	2.39	-		
		$T_{vj}=125^{\circ}C$	-	3.23	-		
		$T_{vj}=150^{\circ}C$	-	3.34	-		
SC data	Short-circuit current	$V_{CC}=600V, V_{GE}\leq 15V, T_{vj}=25^{\circ}C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$		-	245	-	A
R_{thJC}	Thermal resistance, junction to case	Per IGBT		-	-	0.58	K/W
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT / $\lambda_{grease}=1W/(m\cdot K)$		-	0.245	-	K/W
T_{vjop}	Temperature under switching conditions			-40		150	$^{\circ}C$
Diode, Brake-Chopper							
Maximum Rated Values							
Symbol	Item	Conditions			Rating		Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^{\circ}C$			1200		V
I_F	Forward current, DC				25		A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$			50		A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$			170		A^2s
Characteristic Values							
V_F	Continuous forward voltage	$I_F=25A$ $V_{GE}=0V$	$T_{vj}=25^{\circ}C$	-	1.91	2.3	V
			$T_{vj}=125^{\circ}C$	-	1.81	-	
			$T_{vj}=150^{\circ}C$	-	1.79	-	

I _{RM}	Peak reverse recovery current	V _R =600V I _F =50A V _{GE} =-15V -di _F /dt=1800A/μs (T _{vj} =150°C)	T _{vj} =25°C	-	25.3	-	A
			T _{vj} =125°C	-	28.9	-	
			T _{vj} =150°C	-	30.9	-	
t _{rr}	Reverse recovery time		T _{vj} =25°C	-	56.5	-	ns
			T _{vj} =125°C	-	548.1	-	
			T _{vj} =150°C	-	582.6	-	
Q _r	Recovered charge		T _{vj} =25°C	-	1.71	-	μC
			T _{vj} =125°C	-	6.86	-	
			T _{vj} =150°C	-	7.24	-	
E _{rec}	Reverse recovery energy	T _{vj} =25°C	-	0.37	-	mJ	
		T _{vj} =125°C	-	2.98	-		
		T _{vj} =150°C	-	3.31	-		
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	1.45	K/W	
R _{thCH}	Thermal resistance, case to heatsink	per diode / λ _{grease} =1 W/(m • K)	-	0.61	-	K/W	
T _{vjop}	Temperature under switching conditions		-40		150	°C	

Note:

IGBT electrical characteristics according to IEC 60747 – 9

Diode electrical characteristics according to IEC 60747 – 2

NTC Thermistor Characteristics

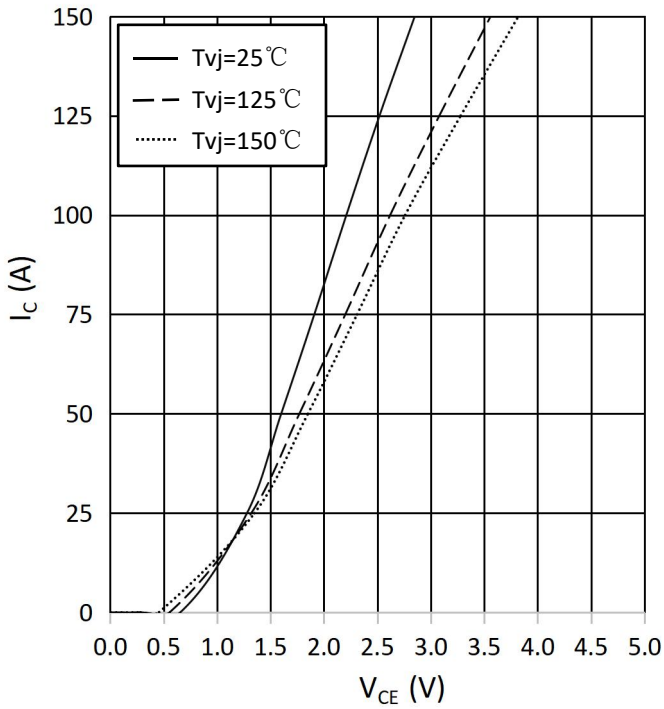
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	-	3375	-	K
B _{25/80}	B-constant	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	-	3411	-	
B _{25/100}	B-constant	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]	-	3433	-	

Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
T _{vj max}	Maximum junction temperature	-	175			°C
T _{vj op}	Operating junction temperature	Continuous operation(underswitching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	-	3	-	6	Nm
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	290	-	g

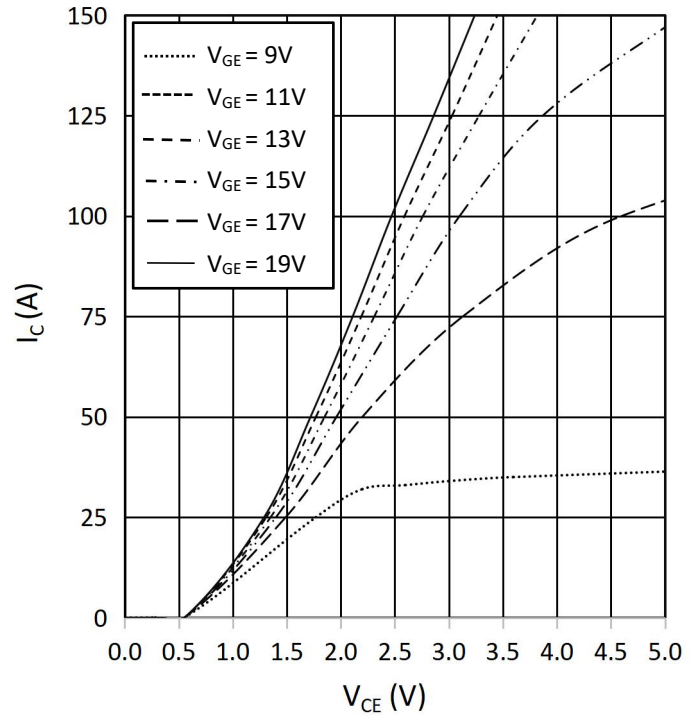
output characteristic IGBT,Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15V$



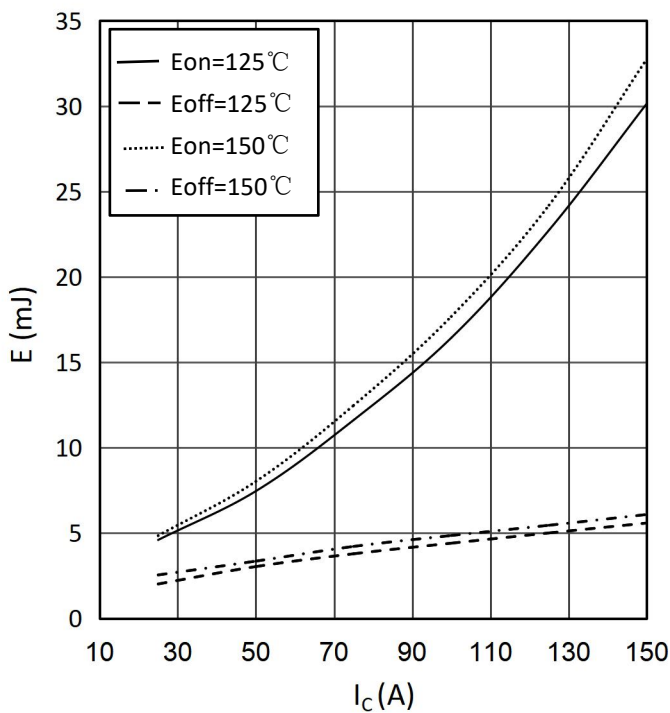
output characteristic IGBT,Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ C$



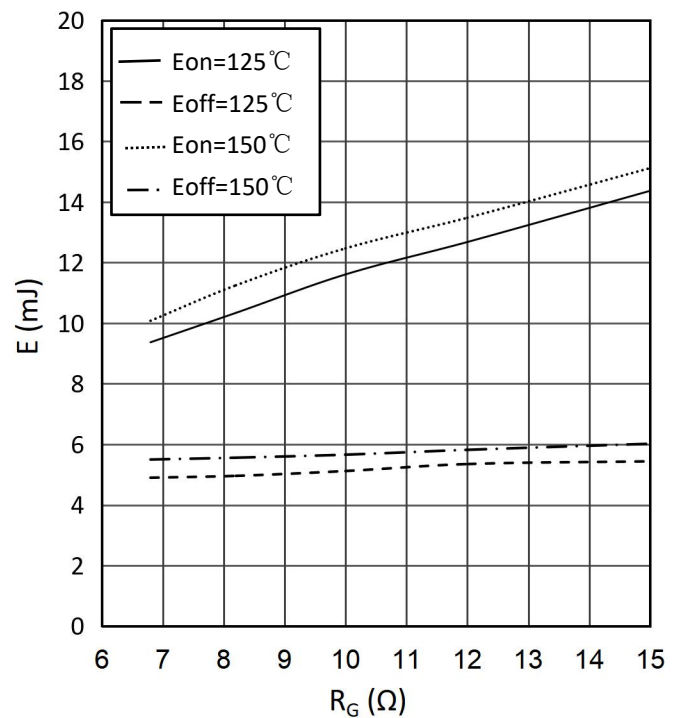
switching losses IGBT,Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15V$, $R_{Gon} = 10\Omega$, $R_{Goff} = 10\Omega$, $V_{CE} = 600V$



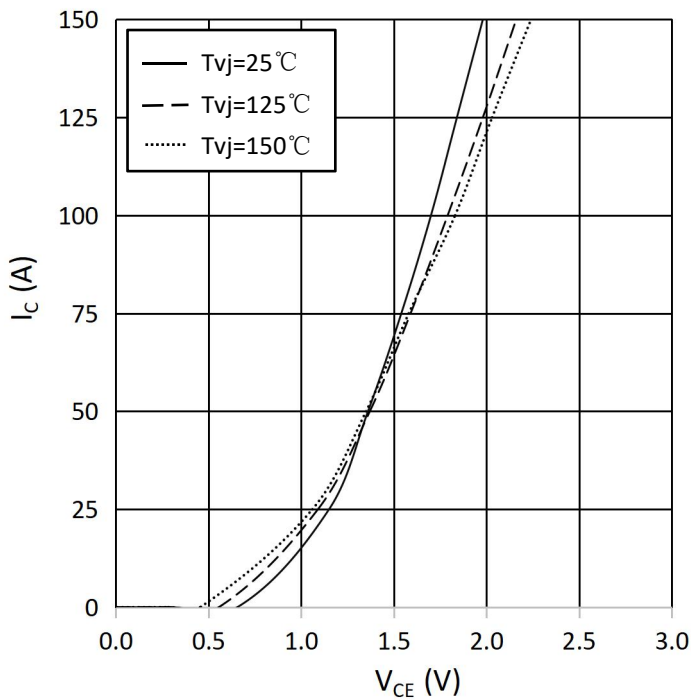
switching losses IGBT,Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15V$, $I_C = 75A$, $V_{CE} = 600V$



forward characteristic of Diode, Inverter (typical)

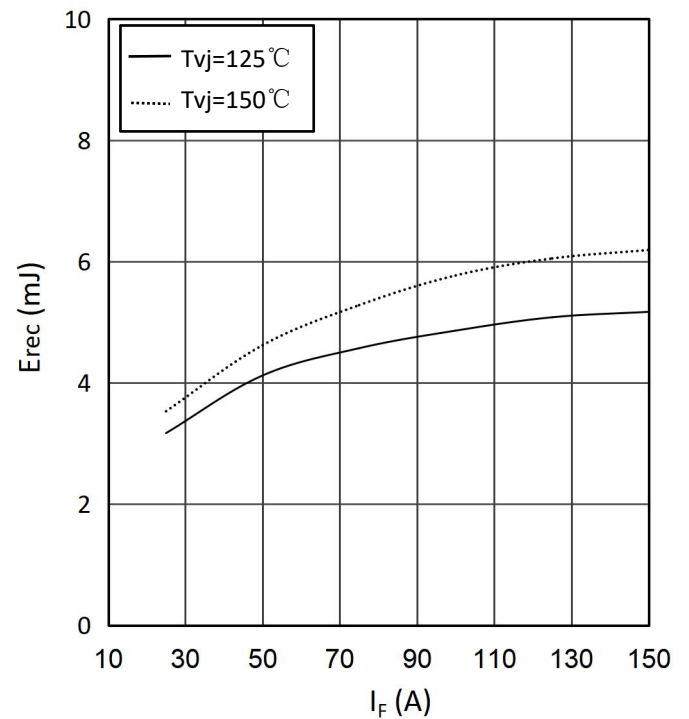
$I_F = f(V_F)$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

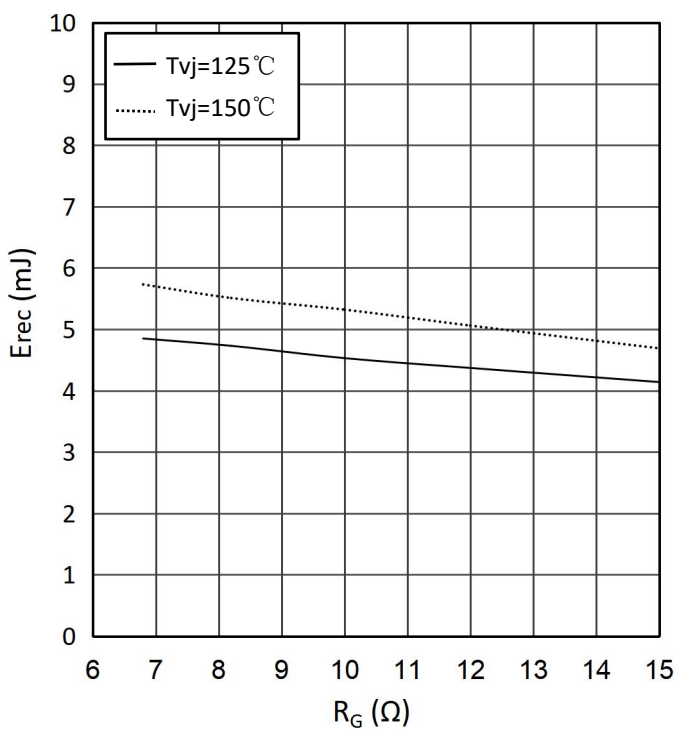
$R_{Gon} = 10\Omega, V_{CE} = 600\text{ V}$



switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$

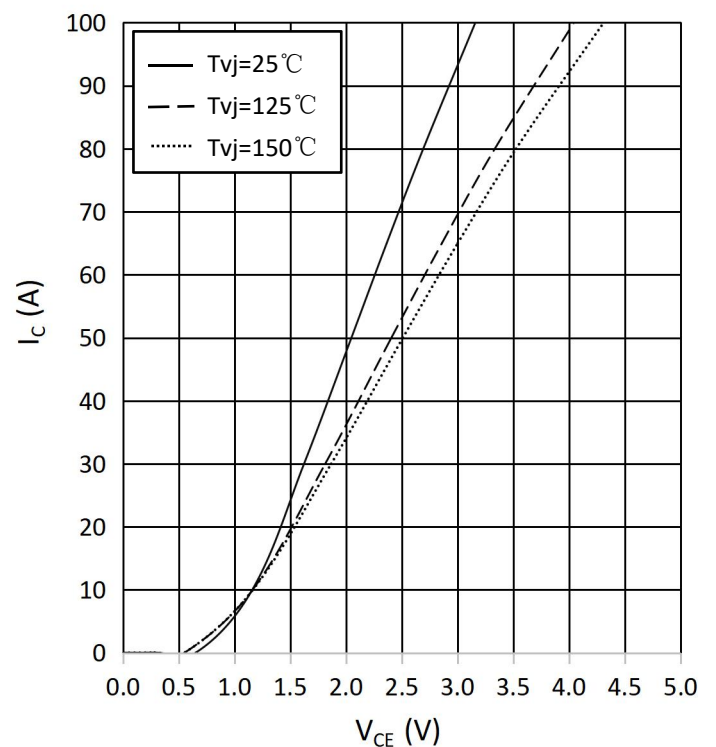
$I_F = 75\text{A}, V_{CE} = 600\text{V}$



output characteristic IGBT, Brake-Chopper (typical)

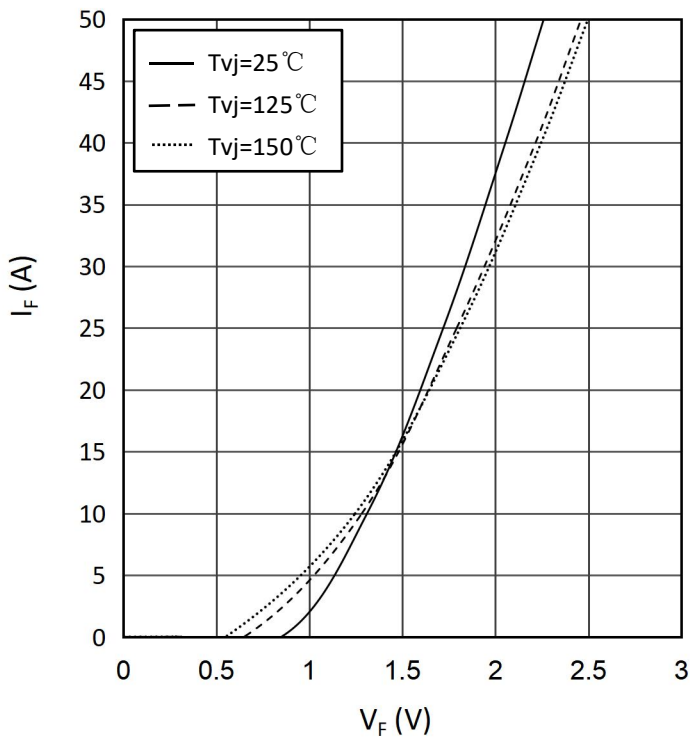
$I_C = f(V_{CE})$

$V_{GE} = 15\text{V}$



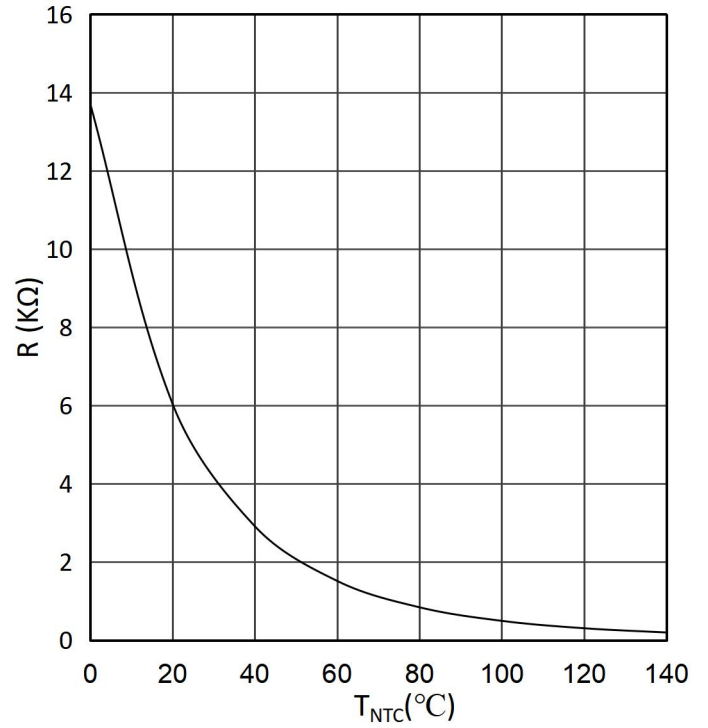
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



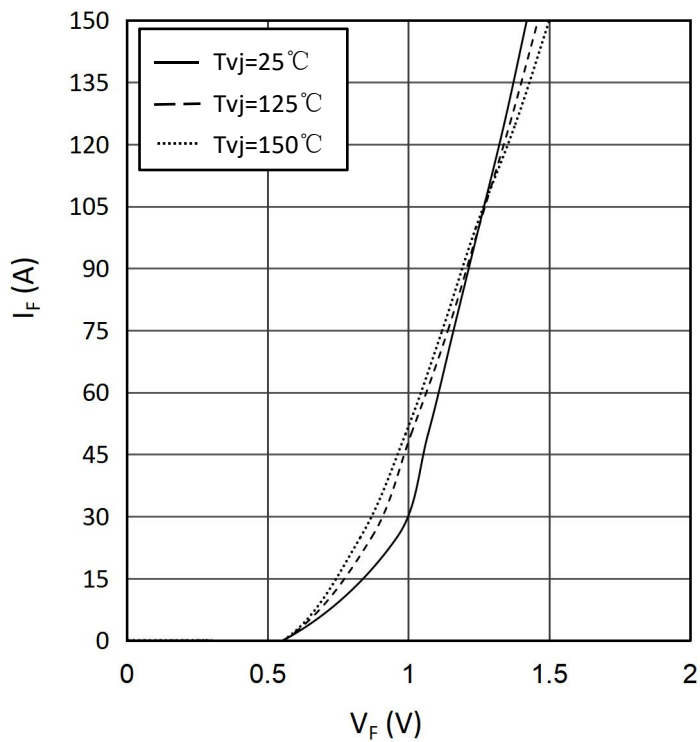
NTC-Thermistor-temperature characteristic(typical)

$R=f(T)$

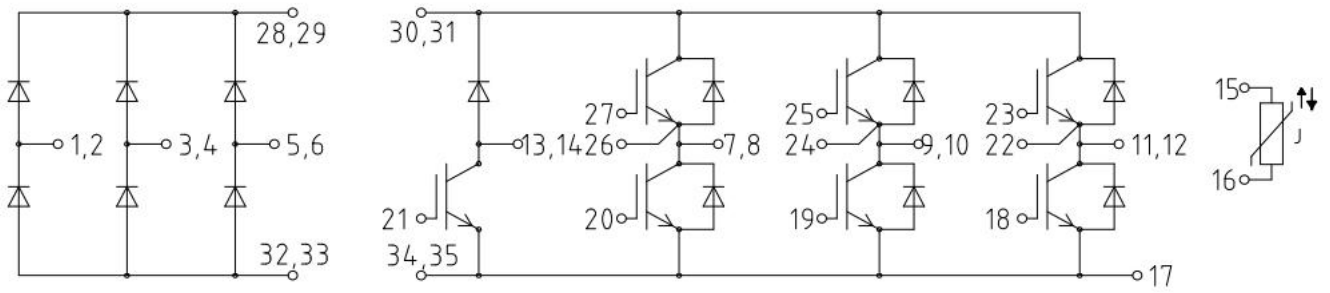


Forward characteristic of Diode, Rectifier(typical)

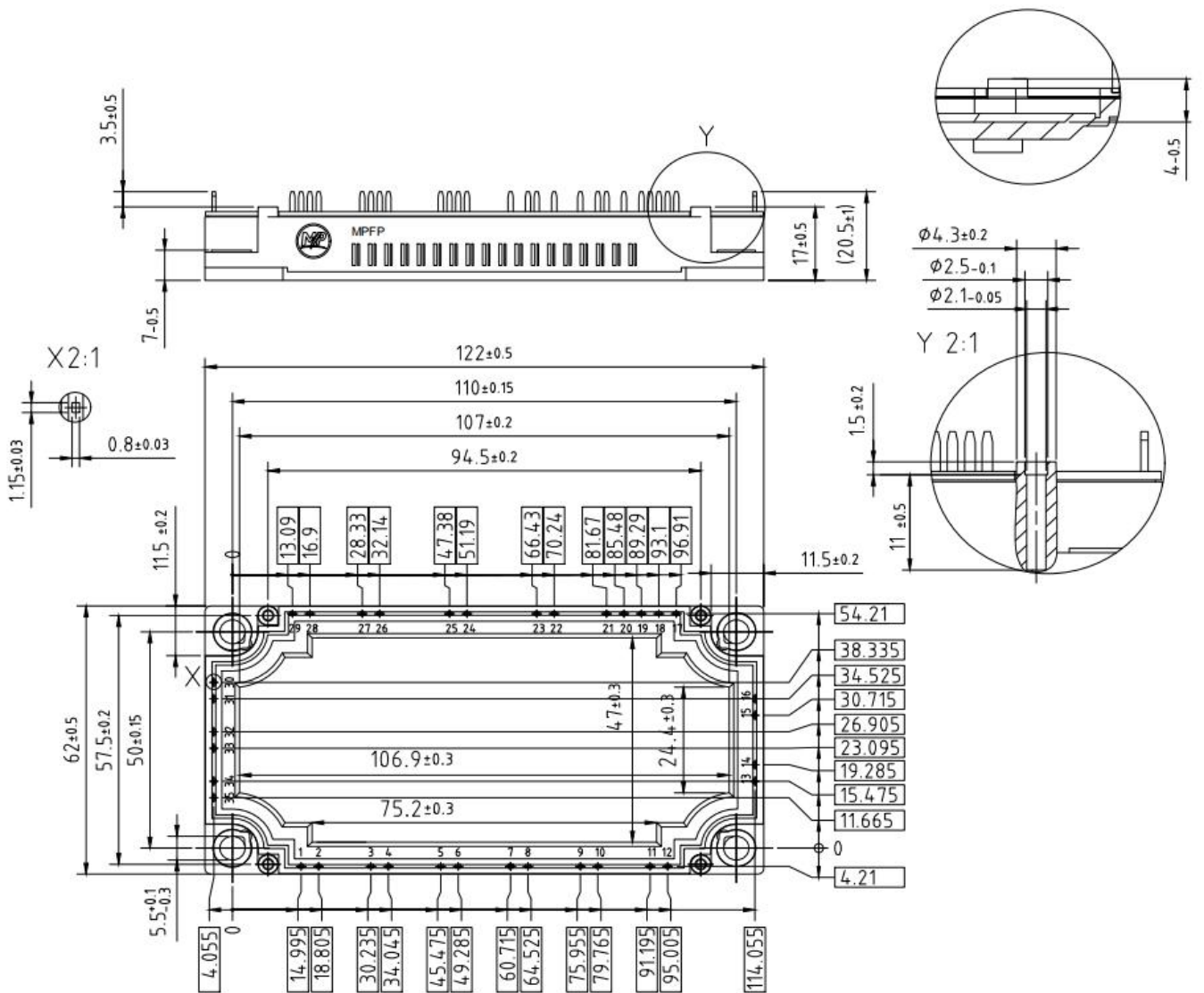
$I_F = f(V_F)$



Circuit Diagram



Package Outlines



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